



# STP7NB80 STP7NB80FP

## N - CHANNEL 800V - 1.2Ω - 6.5A - TO-220/TO-220FP PowerMESH™ MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP7NB80	800 V	< 1.5 Ω	6.5 A
STP7NB80FP	800 V	< 1.5 Ω	6.5 A

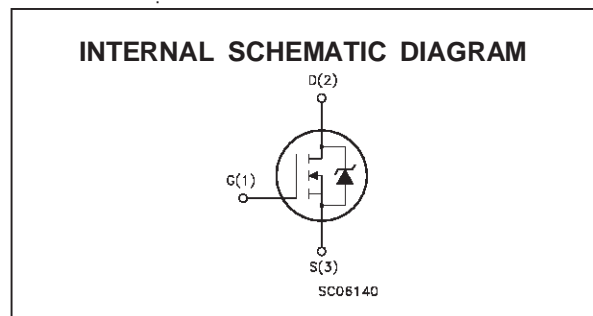
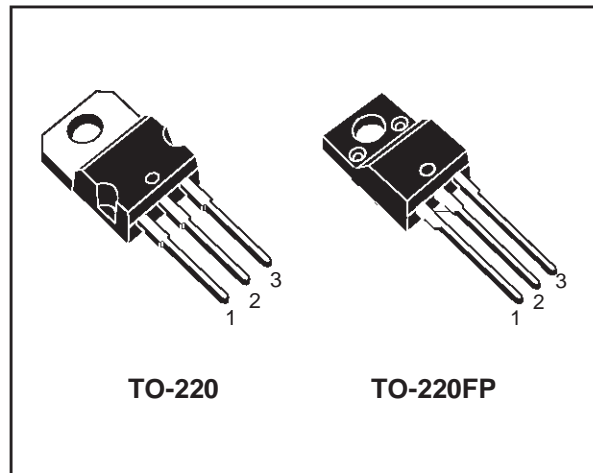
- TYPICAL R<sub>DS(on)</sub> = 1.2 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

### DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest RDS(on) per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP7NB80	STP7NB80FP	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	800		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	800		V
V <sub>GS</sub>	Gate-source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	6.5	6.5(*)	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	4.1	4.1(*)	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	26	26	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	135	40	W
	Derating Factor	1.08	0.32	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.5	4.5	V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	--	2000	°C
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(\*) Limited only maximum temperature allowed

(1) I<sub>SD</sub> ≤ 6.5A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ T<sub>JMAX</sub>

## STP7NB80/FP

### THERMAL DATA

		TO-220	TO-220FP		
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.92	3.13	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	6.5	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	400	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	800			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 3.2 A		1.2	1.5	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	6.5			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 3.2 A	1.5	6.5		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1400		pF
C <sub>oss</sub>	Output Capacitance			180		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			20		pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D = 3.5\text{ A}$		20		ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		10		ns
$Q_g$	Total Gate Charge	$V_{DD} = 640\text{ V}$ $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$		40	52	nC
$Q_{gs}$	Gate-Source Charge	$R_G = 4.7\ \Omega$		10		nC
$Q_{gd}$	Gate-Drain Charge			18		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 7\text{ A}$		15		ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		15		ns
$t_c$	Cross-over Time			25		ns

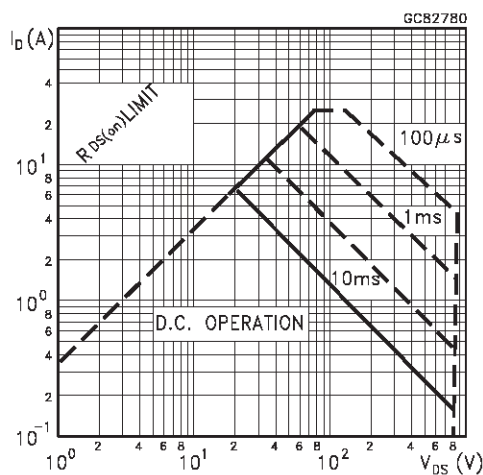
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				6.5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				26	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 6.5\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 7\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		750		ns
$Q_{rr}$	Reverse Recovery Charge			7.10		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			19		A

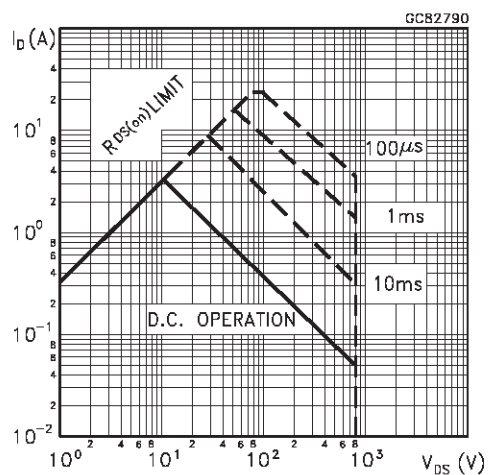
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

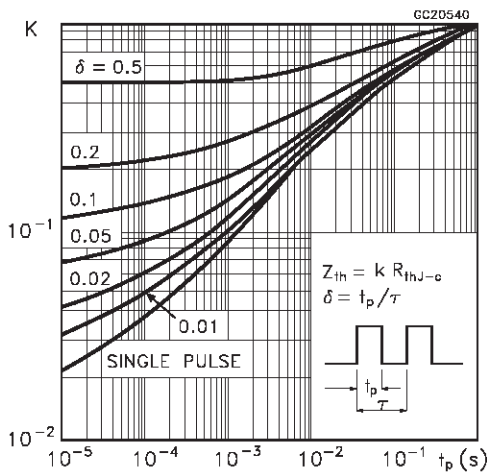
Safe Operating Area for TO-220



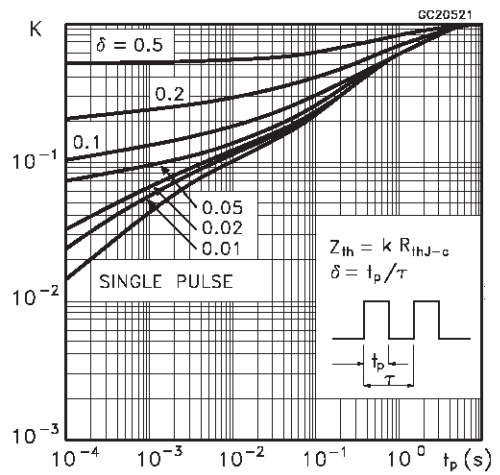
Safe Operating Area for TO-220FP



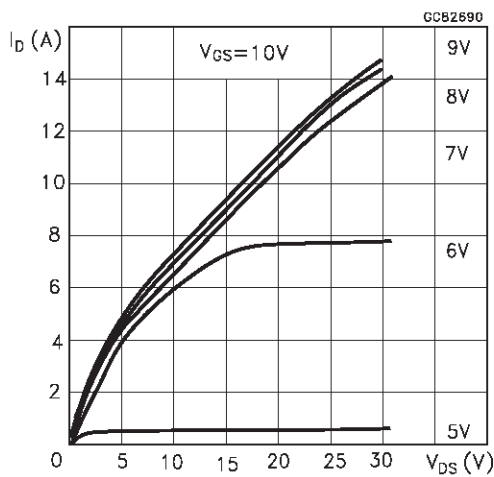
Thermal Impedance for TO-220



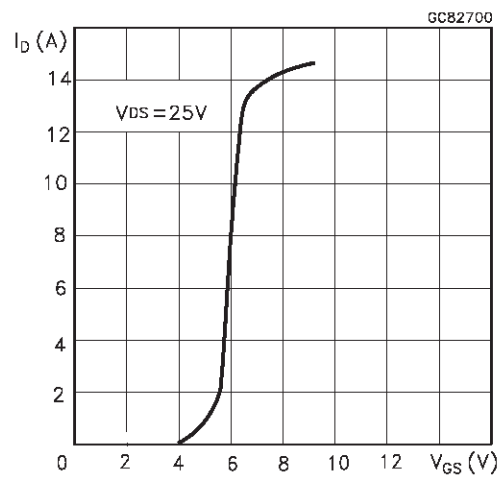
Thermal Impedance for TO-220FP



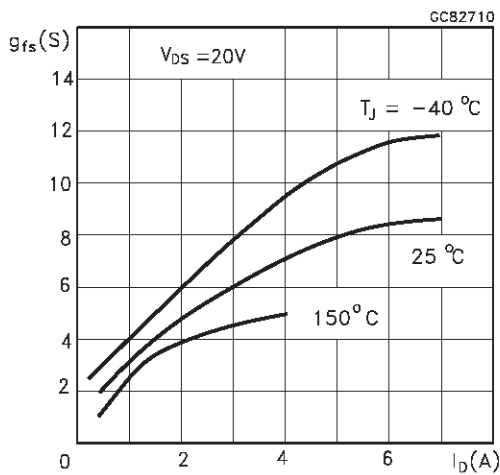
Output Characteristics



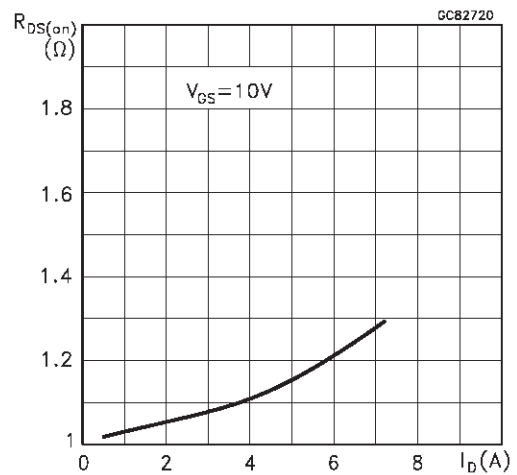
Transfer Characteristics



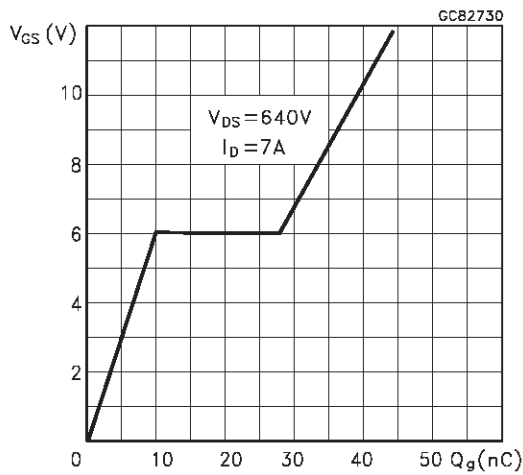
Transconductance



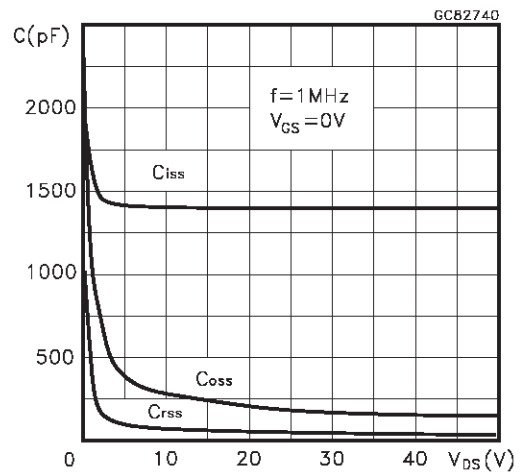
Static Drain-source On Resistance



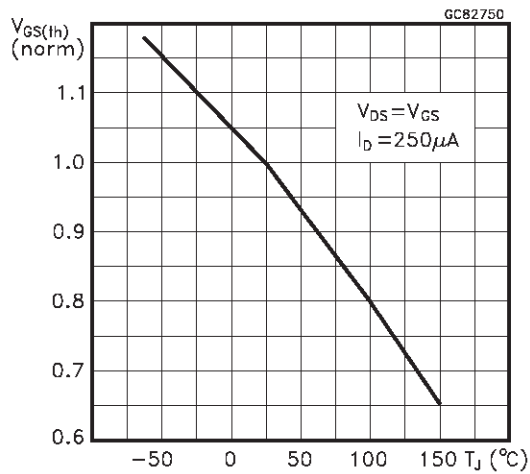
Gate Charge vs Gate-source Voltage



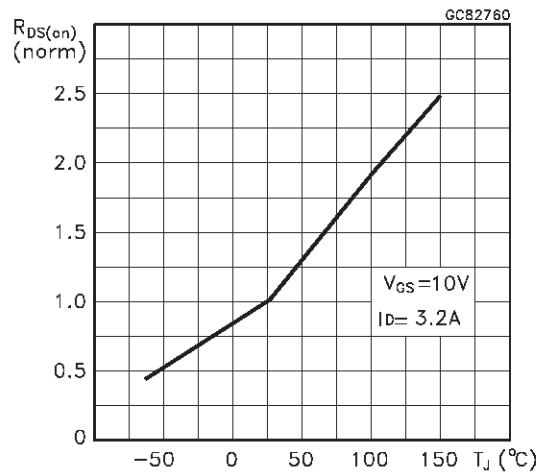
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

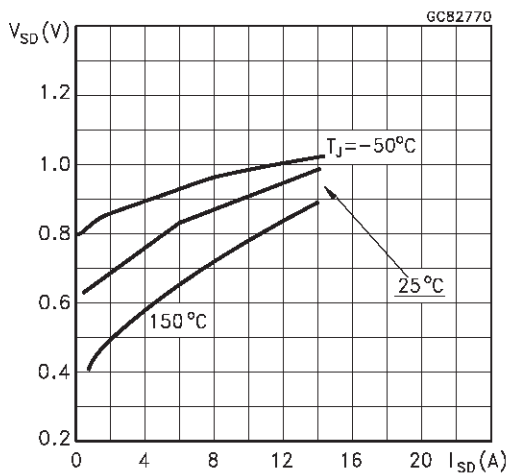


Fig. 1: Unclamped Inductive Load Test Circuit

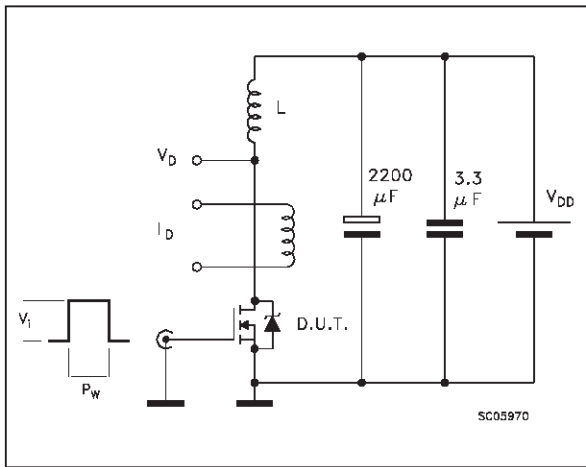


Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load

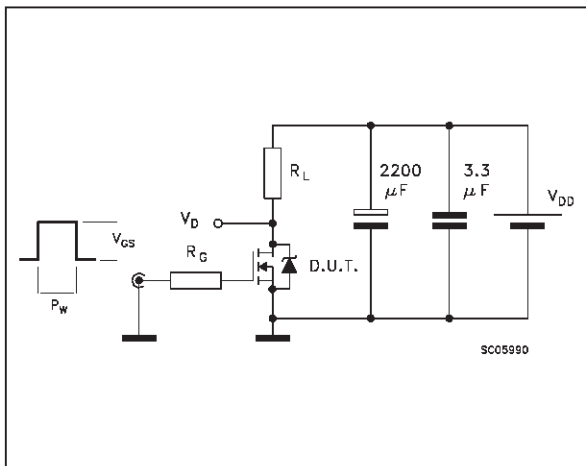


Fig. 4: Gate Charge test Circuit

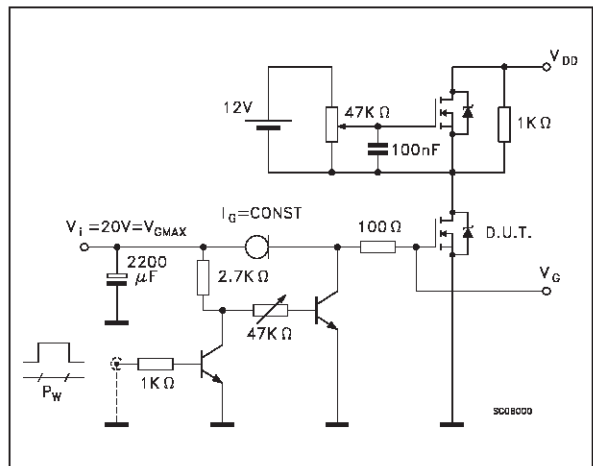
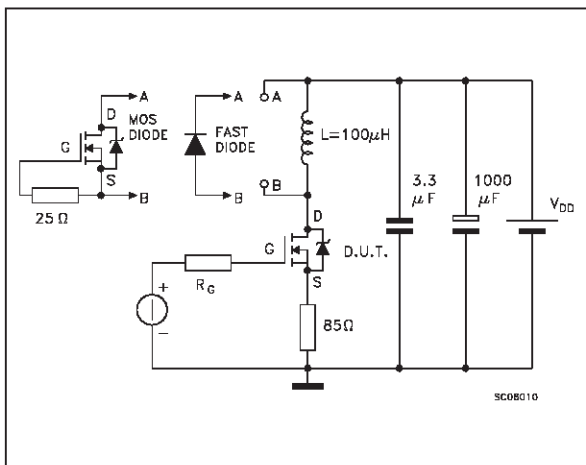
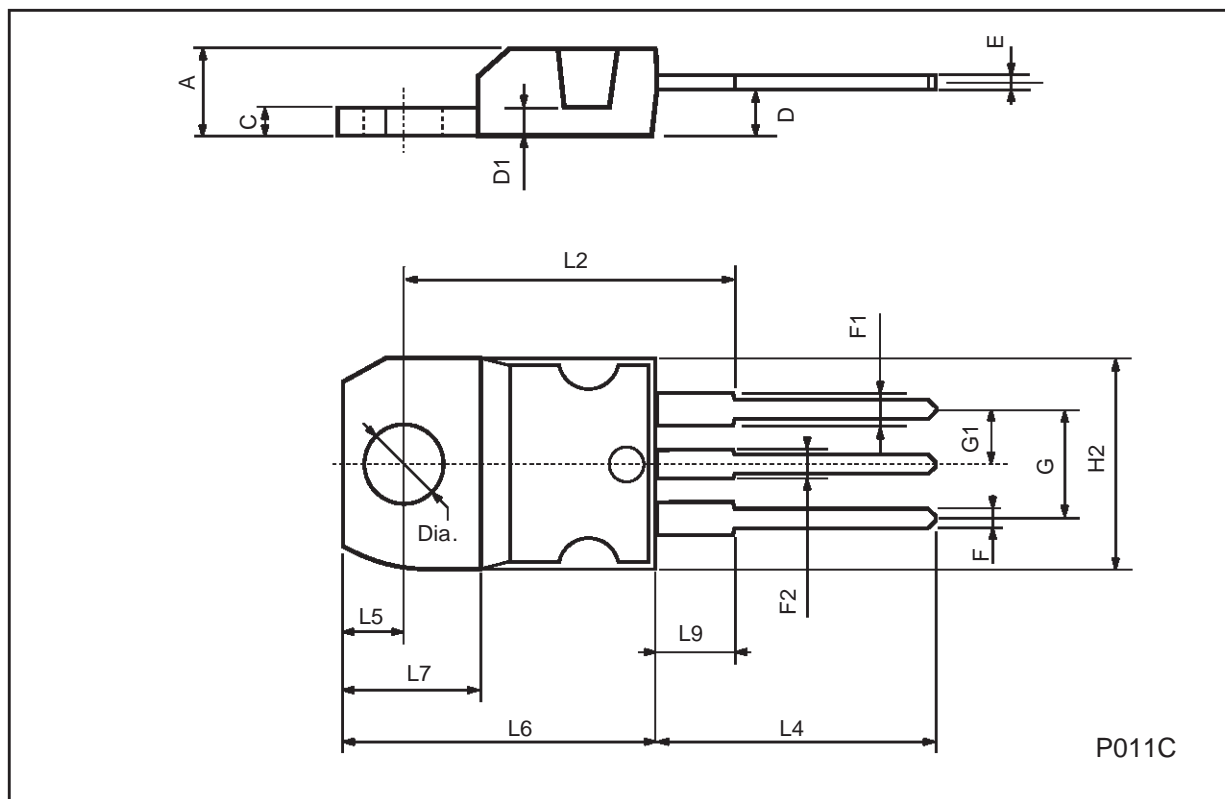


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



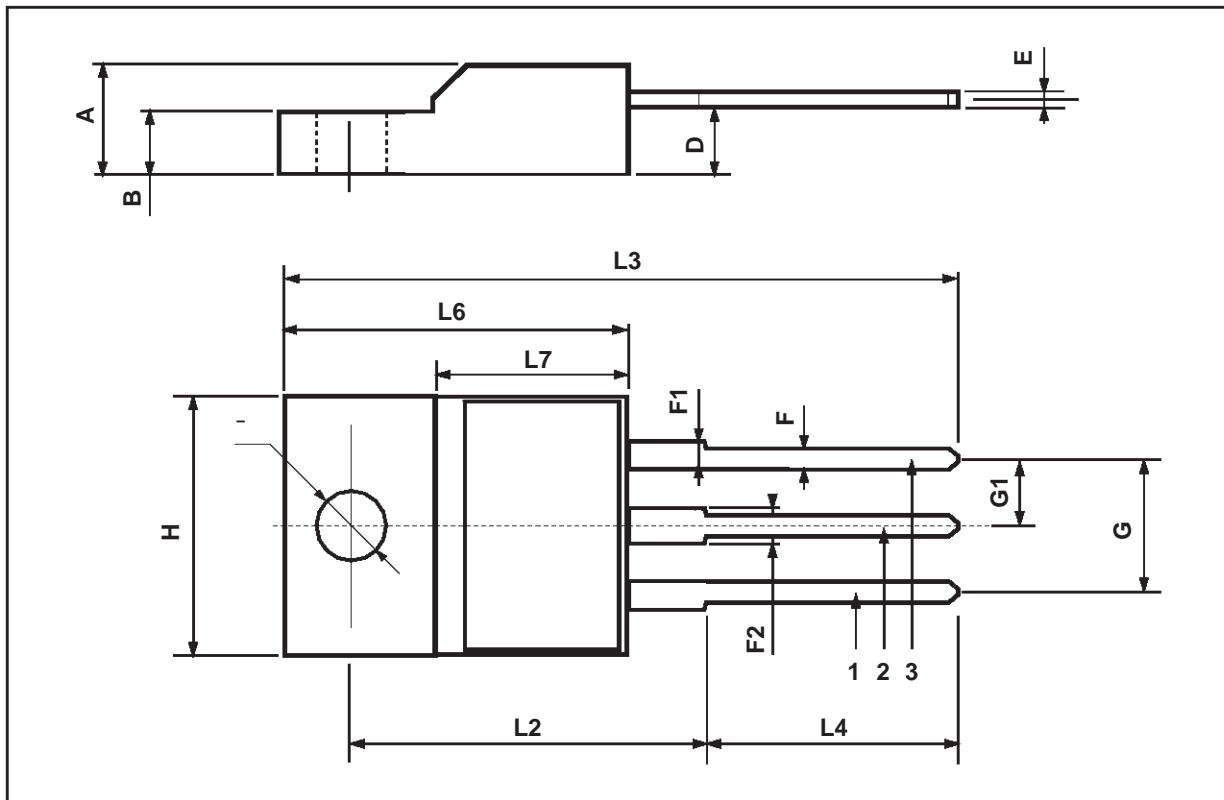
## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126





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